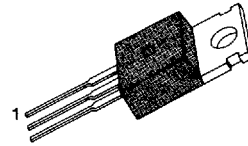


IRF9Z34/30**P-CHANNEL
POWER MOSFETS****FEATURES**

- Lower $R_{DS(on)}$
- Improved inductive ruggedness
- Fast switching times
- Rugged polysilicon gate cell structure
- Lower input capacitance
- Extended safe operating area
- Improved high temperature reliability

TO-220



1. Gate 2. Drain 3. Source

PRODUCT SUMMARY

Part Number	V _{DS}	R _{DS(on)}	I _D
IRF9Z34	-60V	0.14Ω	-18A
IRF9Z30	-50V	0.24Ω	-18A

ABSOLUTE MAXIMUM RATINGS

Characteristic	Symbol	IRF9Z34	IRF9Z30	Unit
Drain-Source Voltage (1)	V _{DSS}	-60	-55	Vdc
Drain-Gate Voltage (R _{GS} =1.0MΩ)(1)	V _{DGR}	-60	-55	Vdc
Gate-Source Voltage	V _{GS}	±20		Vdc
Continuous Drain Current T _c =25 °C	I _D	-18		Adc
Continuous Drain Current T _c =100 °C	I _D	-12.6		Adc
Drain Current - Pulsed (3)	I _{DM}	-72		Adc
Gate Current - Pulsed	I _{GM}	±1.5		Adc
Single Pulsed Avalanche Energy (4)	E _{AS}	13		mJ
Avalanche Current	I _{AS}	-18		A
Total Power Dissipation at T _c =25 °C	P _D	88		Watts
Derate above 25 °C		0.59		W/°C
Operating and Storage Junction Temperature Range	T _J , T _{STG}	-55 to + 175		°C
Maximum Lead Temp. for Soldering Purposes, 1/8" from case for 5 seconds	T _L	300		°C

Notes : (1) T_J=25°C to 175°C

(2) Pulse test : Pulse width ≤ 300μs, Duty Cycle ≤ 2%

(3) Repetitive rating : Pulse width limited by max. junction temperature

(4) L=100μH, V_{dd}=-25V, R_G=25Ω, Starting T_J=25°C

IRF9Z34/30

ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise specified)

Symbol	Characteristic	Min	Typ	Max	Units	Test Conditions
BV _{DSS}	Drain-Source Breakdown Voltage					
	IRF9Z34	-60	-	-	V	V _{GS} =0V, I _D =-250μA
	IRF9Z30	-50	-	-	V	
V _{GS(th)}	Gate Threshold Voltage	-2.0	-	-4.0	V	V _{DS} =V _{GS} , I _D =-250μA
I _{GSS}	Gate-Source Leakage Forward	-	-	-100	nA	V _{GS} =-20V
I _{GSS}	Gate-Source Leakage Reverse	-	-	100	nA	V _{GS} =20V
I _{DSS}	Zero Gate Voltage Drain Current	-	-	-250	μA	V _{DS} =-Max. Rating, V _{GS} =0V
		-	-	-1000	μA	V _{DS} =-0.8 Max. Rating, T _C =125°C
R _{DS(on)}	Static Drain-Source On Resistance(2)	-	0.10	0.14	Ω	V _{GS} =-10V, I _D =-9.0A
g _{fs}	Forward Transconductance (2)	3.1	7.3	-	Ω	V _{DS} =2xV _{GS} , I _D =-9.0A
C _{iss}	Input Capacitance	-	1196	-	pF	V _{GS} =0V, V _{DS} =-25V, f=1.0MHz
C _{oss}	Output Capacitance	-	444	-	pF	
C _{rss}	Reverse Transfer Capacitance	-	232	-	pF	
t _{d(on)}	Turn-On Delay Time	-	12	18	ns	V _{DD} =-25V, I _D =-18A, R _G =18Ω (MOSFET switching times are essentially independent of operating temperature)
t _r	Rise Time	-	110	170	ns	
t _{d(off)}	Turn-Off Delay Time	-	21	32	ns	
t _f	Fall Time	-	64	96	ns	
Q _g	Total Gate Charge (Gate-Source Plus Gate-Drain)	-	-	63	nC	V _{GS} =-10V, I _D =-18A, V _{DS} =-0.8 Max. Rating (Gate charge is essentially independent of operating temperature)
Q _{gs}	Gate-Source Charge	-	14.6	-	nC	
Q _{gd}	Gate-Drain ("Miller") Charge	-	20.6	-	nC	

THERMAL RESISTANCE


Symbol	Characteristics		All	Units	Remark
R _{thJC}	Junction-to-Case	MAX	1.67	K/W	
R _{thCS}	Case-to-Sink	TYP	0.5	K/W	Mounting surface flat smooth, and greased
R _{thJA}	Junction-to-Ambient	MAX	62.5	K/W	Free Air Operation

Notes : (1) T_J=25°C to 175°C

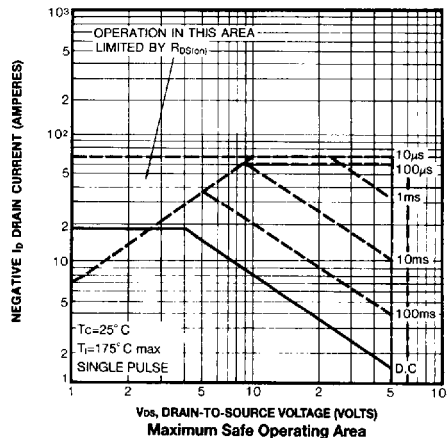
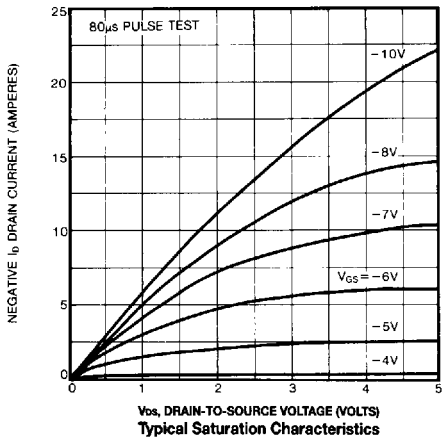
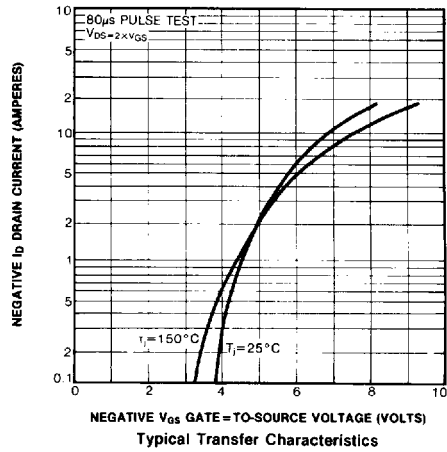
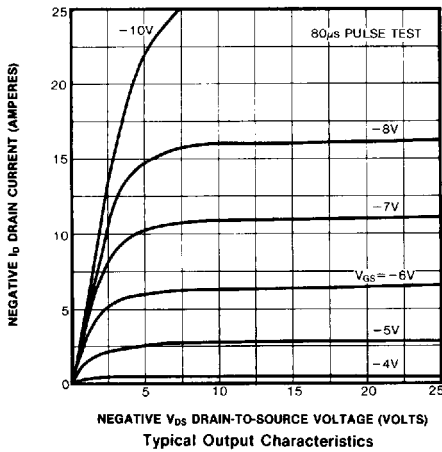
(2) Pulse test : Pulse width ≤ 300μs, Duty Cycle ≤ 2%

(3) Repetitive rating : Pulse width limited by max. junction temperature

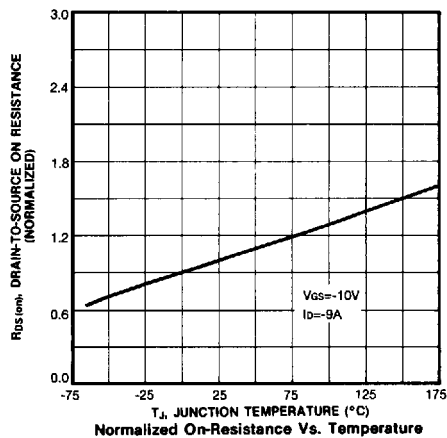
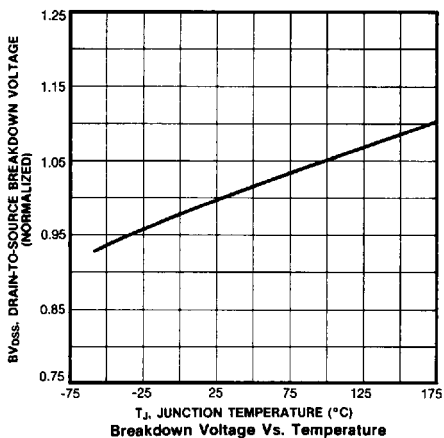
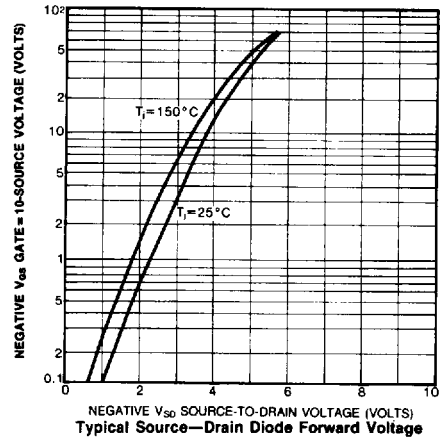
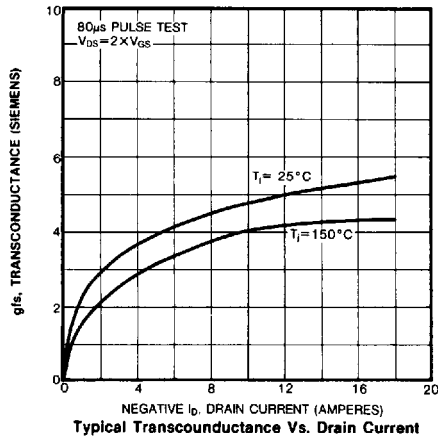
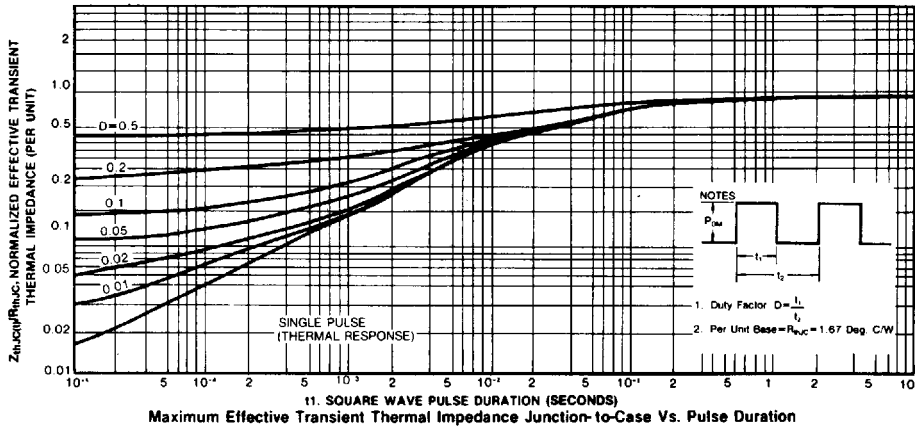
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

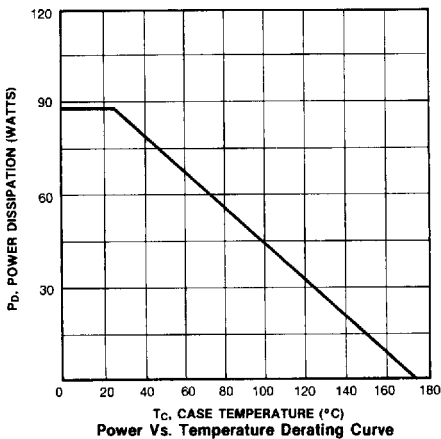
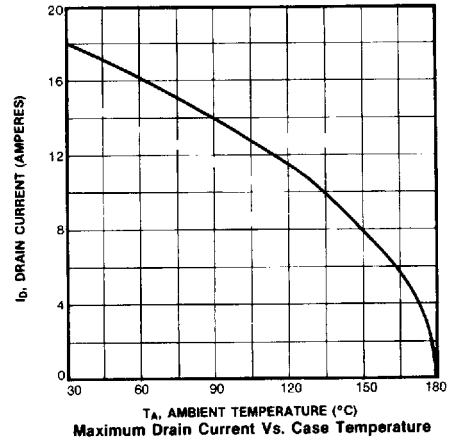
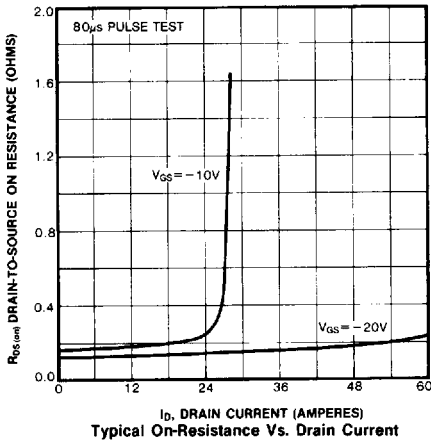
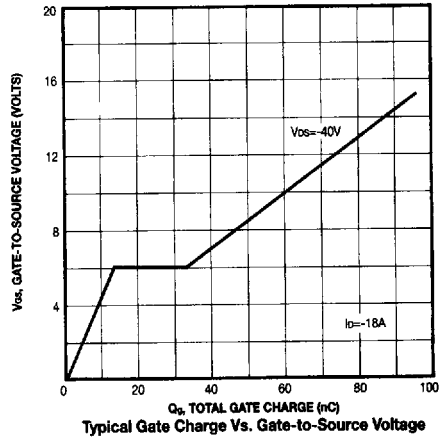
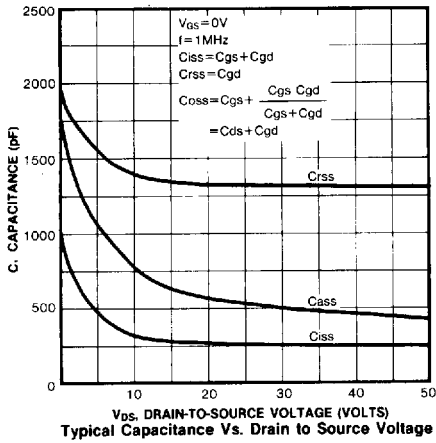
Symbol	Characteristic	Min	Typ	Max	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	-	-	-18	A	Modified MOSFET symbol showing the integral reverse P-N junction rectifier 
I_{SM}	Pulse Source Current (Body Diode) (3)	-	-	-72	A	
V_{SD}	Diode Forward Voltage (2)	-	-	-6.3	V	$T_J=25^\circ\text{C}$, $I_S=-18\text{A}$, $V_{GS}=0\text{V}$
t_{rr}	Reverse Recovery Time	-	-	250	ns	$T_J=25^\circ\text{C}$, $I_F=-18\text{A}$, $dI_F/dt=100\text{A}/\mu\text{S}$

- Notes : (1) $T_J=25^\circ\text{C}$ to 175°C
 (2) Pulse test : Pulse width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$
 (3) Repetitive rating : Pulse width limited by max. junction temperature



4





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